

EMF23XV6T5

Dual Transistor - Power Management

NPN/PNP Dual (Complementary)

Features

- Low $V_{CE(SAT)}$, < 0.5 V
- These are Pb-Free Devices

MAXIMUM RATINGS

Q1

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

Q2

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-60	V
Collector - Base Voltage	V_{CBO}	-50	V
Emitter - Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	357 (Note 1) 2.9 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	500 (Note 1) 4.0 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 1)	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

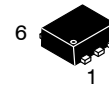
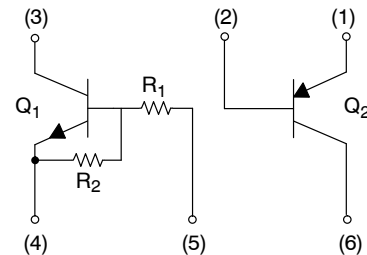
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ Minimum Pad.



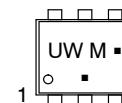
ON Semiconductor®

<http://onsemi.com>



SOT-563
CASE 463A
STYLE 1

MARKING DIAGRAM



UW = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
EMF23XV6T5	SOT-563 (Pb-Free)	8000/Tape & Reel
EMF23XV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Q1: NPN					
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	–	–	0.5	mAdc
Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 3) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	–	–	Vdc
DC Current Gain (V _{CE} = 10 V, I _C = 5.0 mA)	h _{FE}	35	60	–	–
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	–	–	0.25	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 kΩ)	V _{OL}	–	–	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	V _{OH}	4.9	–	–	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	–

Q2: PNP

Collector-Base Breakdown Voltage (I _C = –50 μAdc, I _E = 0)	V _{(BR)CBO}	–60	–	–	Vdc
Collector-Emitter Breakdown Voltage (I _C = –1.0 mAdc, I _B = 0)	V _{(BR)CEO}	–50	–	–	Vdc
Emitter-Base Breakdown Voltage (I _E = –50 μAdc, I _C = 0)	V _{(BR)EBO}	–6.0	–	–	Vdc
Collector-Base Cutoff Current (V _{CB} = –30 Vdc, I _E = 0)	I _{CBO}	–	–	–0.5	nA
Emitter-Base Cutoff Current (V _{EB} = –5.0 Vdc, I _B = 0)	I _{EBO}	–	–	–0.5	μA
Collector-Emitter Saturation Voltage (Note 3) (I _C = –50 mAdc, I _B = –5.0 mAdc)	V _{CE(sat)}	–	–	–0.5	Vdc
DC Current Gain (Note 3) (V _{CE} = –6.0 Vdc, I _C = –1.0 mAdc)	h _{FE}	120	–	560	–
Transition Frequency (V _{CE} = –12 Vdc, I _C = –2.0 mAdc, f = 30 MHz)	f _T	–	140	–	MHz
Output Capacitance (V _{CB} = –12 Vdc, I _E = 0 Adc, f = 1.0 MHz)	C _{OB}	–	3.5	–	pF

- Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.
- Pulse Test: Pulse Width ≤ 300 μs, DC ≤ 2%.

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TYPICAL ELECTRICAL CHARACTERISTICS — Q1, NPN

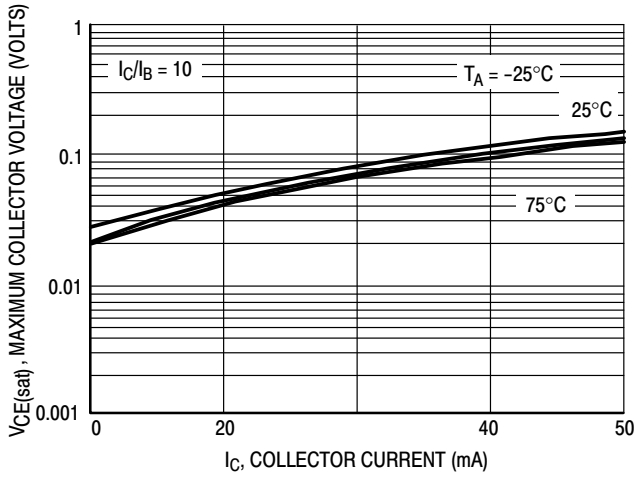


Figure 1. $V_{CE(sat)}$ versus I_C

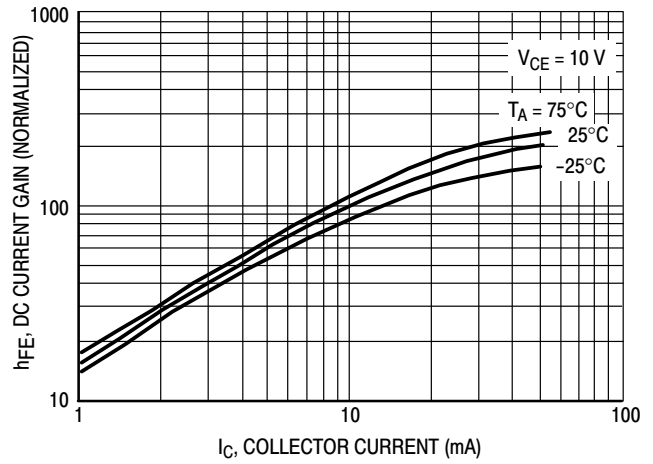


Figure 2. DC Current Gain

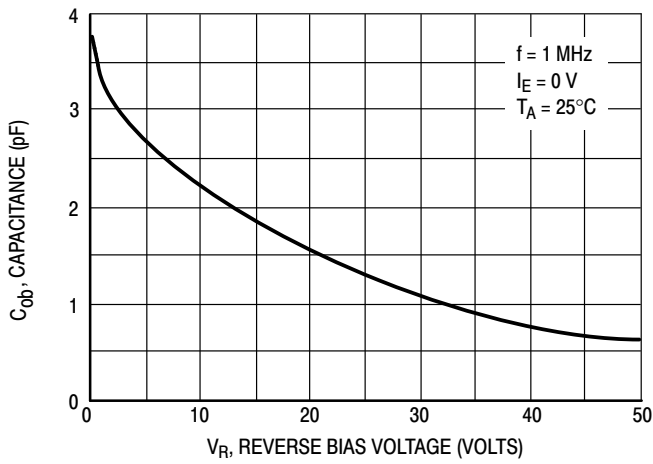


Figure 3. Output Capacitance

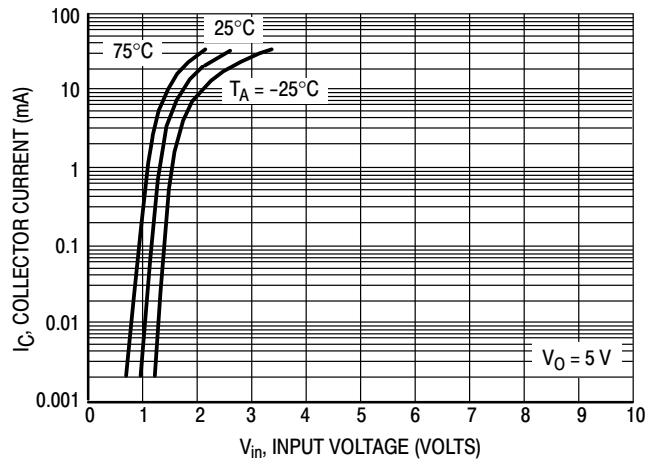


Figure 4. Output Current versus Input Voltage

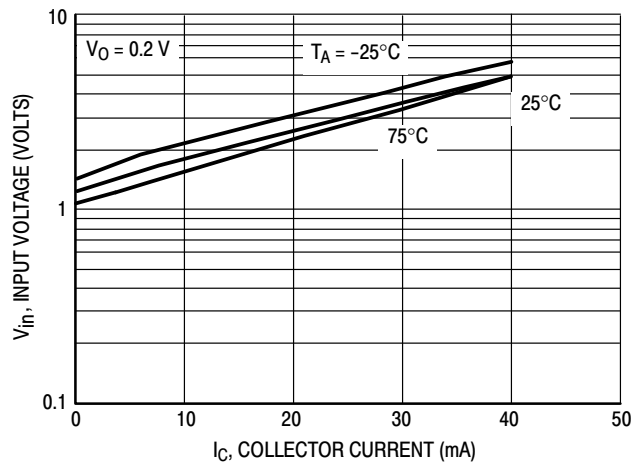


Figure 5. Input Voltage versus Output Current

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TYPICAL ELECTRICAL CHARACTERISTICS – Q2, PNP

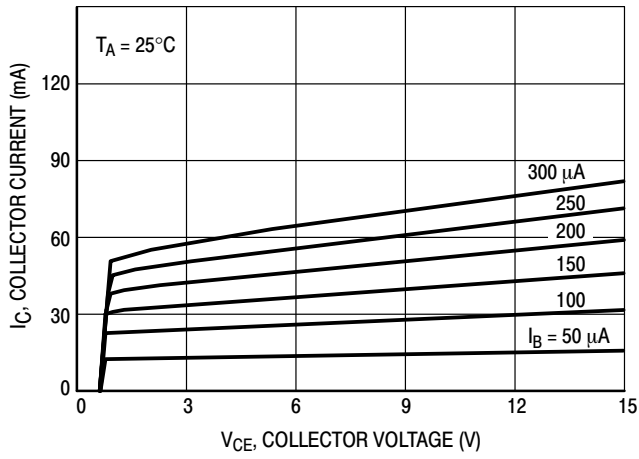


Figure 6. $I_C - V_{CE}$

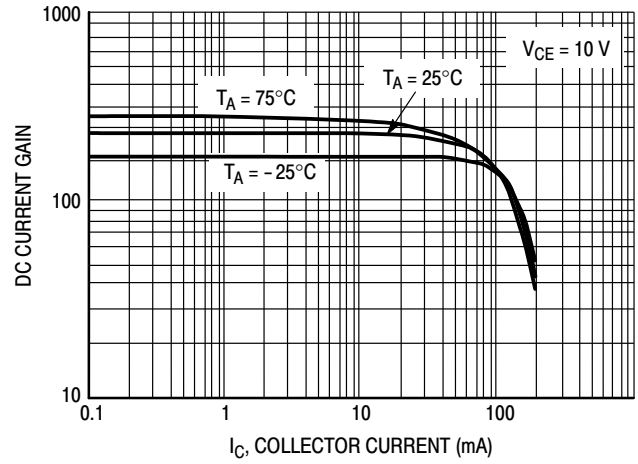


Figure 7. DC Current Gain

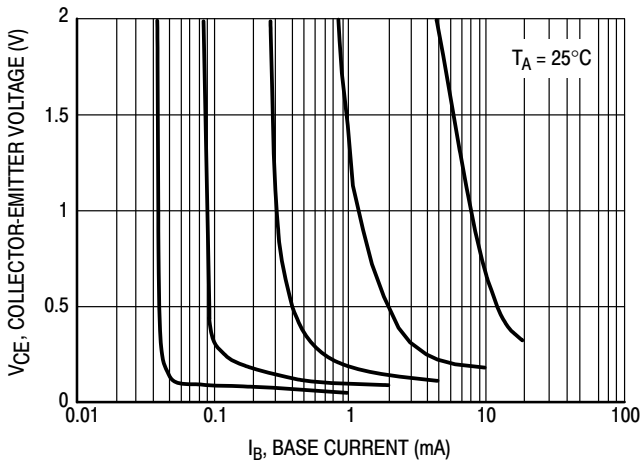


Figure 8. Collector Saturation Region

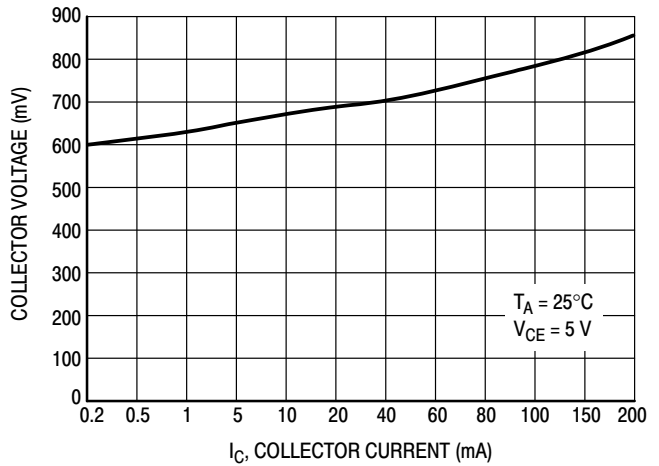


Figure 9. On Voltage

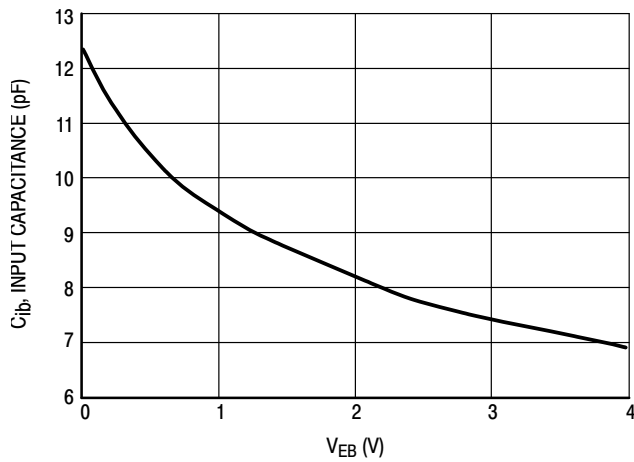


Figure 10. Capacitance

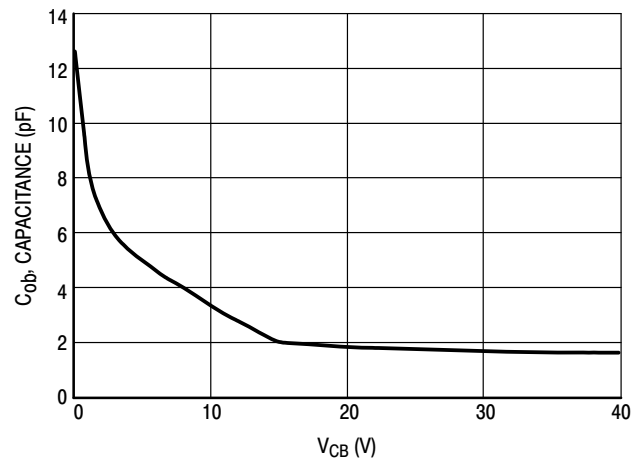
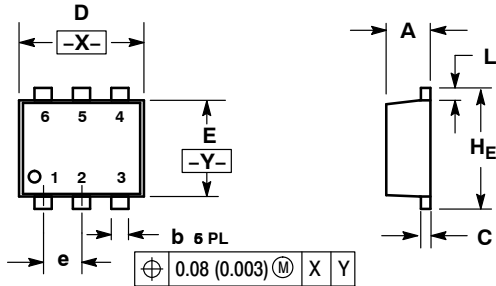


Figure 11. Capacitance

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PACKAGE DIMENSIONS

SOT-563, 6 LEAD
CASE 463A-01
ISSUE F



NOTES:

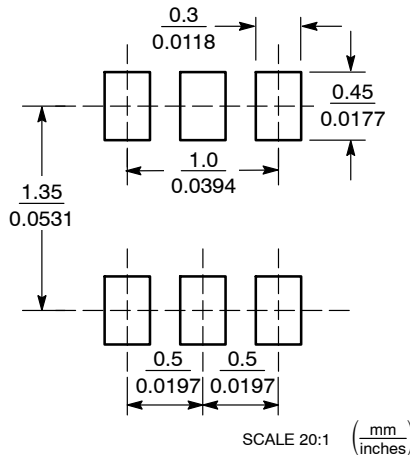
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	1.50	1.60	1.70	0.059	0.062	0.066

STYLE 1:

- PIN 1. EMITTER 1
- BASE 1
- COLLECTOR 2
- EMITTER 2
- BASE 2
- COLLECTOR 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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